

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

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PATENT NO. : 6,939,756
APPLICATION NO. : 09/818,193
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INVENTOR(S) : Gilyong Chung et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Title:

“Inclusion Of Nitrogen At The Silicon Dioxide-Silicon Carbide Interface For Passivation Of Interface Defects” **should read** -- Inclusion Of Nitrogen At The Silicon Dioxide-Silicon Carbide Interface For Passivation Of Interface Defects--.